REMARKS

- (1) Claims 1-18 are pending in the present application. Applicant amended Claim 1 herein, but no new matter has been added.
- (2) The Office Action cited the following reference:
- U. S. Patent 6,297,108 B1, by Chu, entitled *Method Of Forming A High Voltage MOS Transistor On A Semiconductor Wafer* (referred to as "Chu" hereinafter);
- (3) Claims 1,2 and 5-11 were rejected under 35 U.S.C. § 102(b) as assertedly being anticipated by Chu. Applicant respectfully traverses these rejections for the following reasons.

Chu does not disclose, teach, suggest, or motivate a step of "forming a second doped region" "wherein the gate-side boundary of the second doped region is separated from a closest edge of the spacer by a second spaced distance," "and wherein the spacer does not cover the second doped region," as Claim 1 now requires. Because Chu does not disclose these aspects required by Claim 1, Chu cannot anticipate the invention of Claim 1.

Because Claims 2 and 5-11 depend from Claim 1, Applicant respectfully submits that Claims 2 and 5-11 are patentable over Chu for at least the same reasons discussed above for Claim 1. Thus, Applicant respectfully asserts that Claims 1, 2, and 5-11 are patentable over Chu.

(4) Claims 3, 4, and 12-14 were objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. Claims 3, 4, and 12-14 depend from Claim 1. Because Claim 1 is now allowable (as discussed above), Applicant respectfully asserts that the objection to Claims 3, 4, and 12-14 is now overcome.

(5) In view of the above, Applicant respectfully submits that the application is in condition for allowance and requests that the case be passed to issuance. If the Examiner should have any questions, Applicant requests that the Examiner contact Applicant's attorney at the address below. No fees are due with this amendment. In the event that there are any fees due herein to keep the application pending, other than an issue fee, please charge the same, or credit any overpayment, to Deposit Account No. 50-1065.

Respectfully submitted,

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